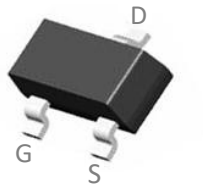
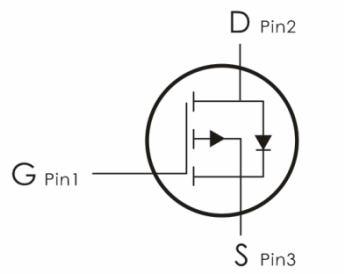
Description：

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.





Features：

1) V_{DS}=-30V,I_D=-5.2A,$R_{DS(ON)}$<40mΩ @V_{GS}=-10V（Typ：31mΩ）
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity trench technology for ultra low $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.
6) MSL3

Package Marking and Ordering Information：

Part NO.	Marking	Package	Packing
DO3401A	3401A	SOT-23	3000 pcs/Reel

Absolute Maximum Ratings：(T_A=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Continuous Drain Current-T_A=25℃[1]	-5.2	A
	Continuous Drain Current-T_A=100℃[1]	-3.6	
I_{DM}	Pulsed Drain Current[2]	-20.8	
P_D	Power Dissipation	1	W
E_{AS}	Single pulse avalanche energy[3]	16.5	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	125	℃/W

Electrical Characteristics: (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	-30	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=-30V	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±12V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	-0.7	-0.86	-1.2	V
$R_{DS(ON)}$	Drain-Source On Resistance[4]	V_{GS}=-10V,I_D=-4.4A	---	31	40	mΩ
		V_{GS}=-4.5V,I_D=-4A	---	34	45	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-15V, V_{GS}=0V, f=1MHz	---	1061	---	pF
C_{oss}	Output Capacitance		---	84	---	
C_{rss}	Reverse Transfer Capacitance		---	71	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=-15V, I_D=-4.4A, R_{ENG}=3Ω ,V_{GS}=-10V	---	4.4	---	ns
t_r	Rise Time		---	27	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	51.6	---	ns
t_f	Fall Time		---	45	---	ns
Q_g	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-15V, I_D=-4.4A	---	10	---	nC
Q_{gs}	Gate-Source Charge		---	3.4	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	2.2	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_{SD}=-4.4A	---	---	-1.2	V
I_S	Continuous Drain Curren	V_D=V_G=0V	---	---	-5.2	A
I_{SM}	Pulsed Drain Current		---	---	-20.8	A
Trr	Reverse Recovery Time	I_F=4.4A,T_J=25℃ dI/dt=100A/us	---	16	---	ns
Qrr	Reverse Recovery Charge		---	10	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : TJ=25℃,VDD=-15V,V_G=-10V,L=0.1mH
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Test Circuit

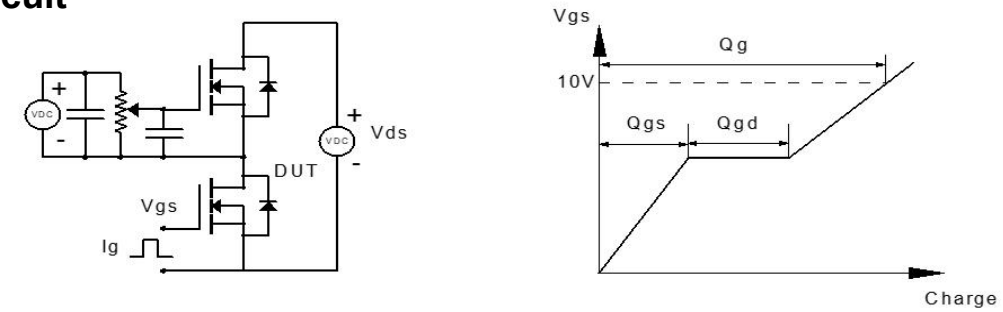


Figure 1: Gate Charge Test Circuit & Waveform

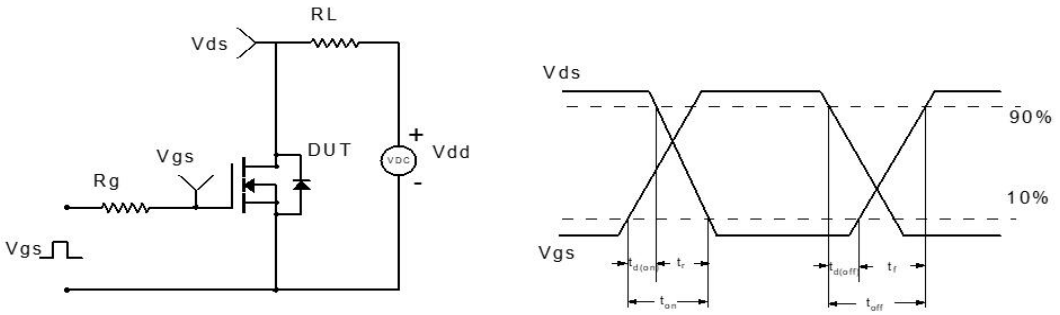


Figure 2: Resistive Switching Test Circuit & Waveform

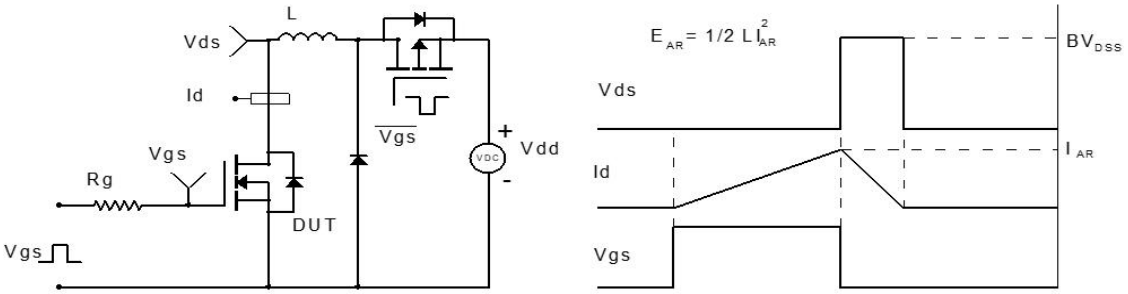


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

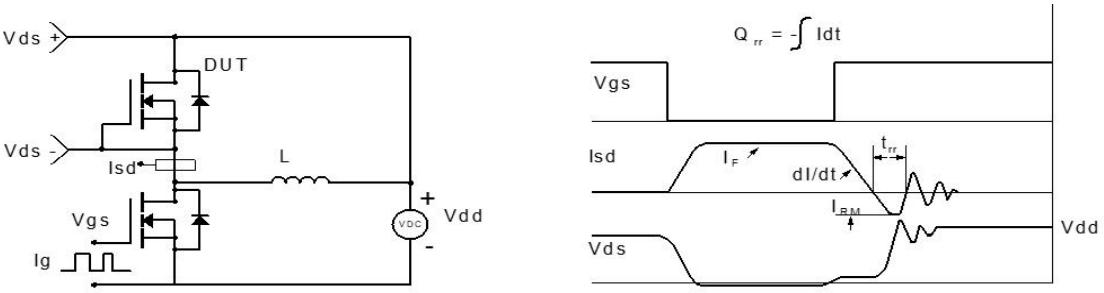
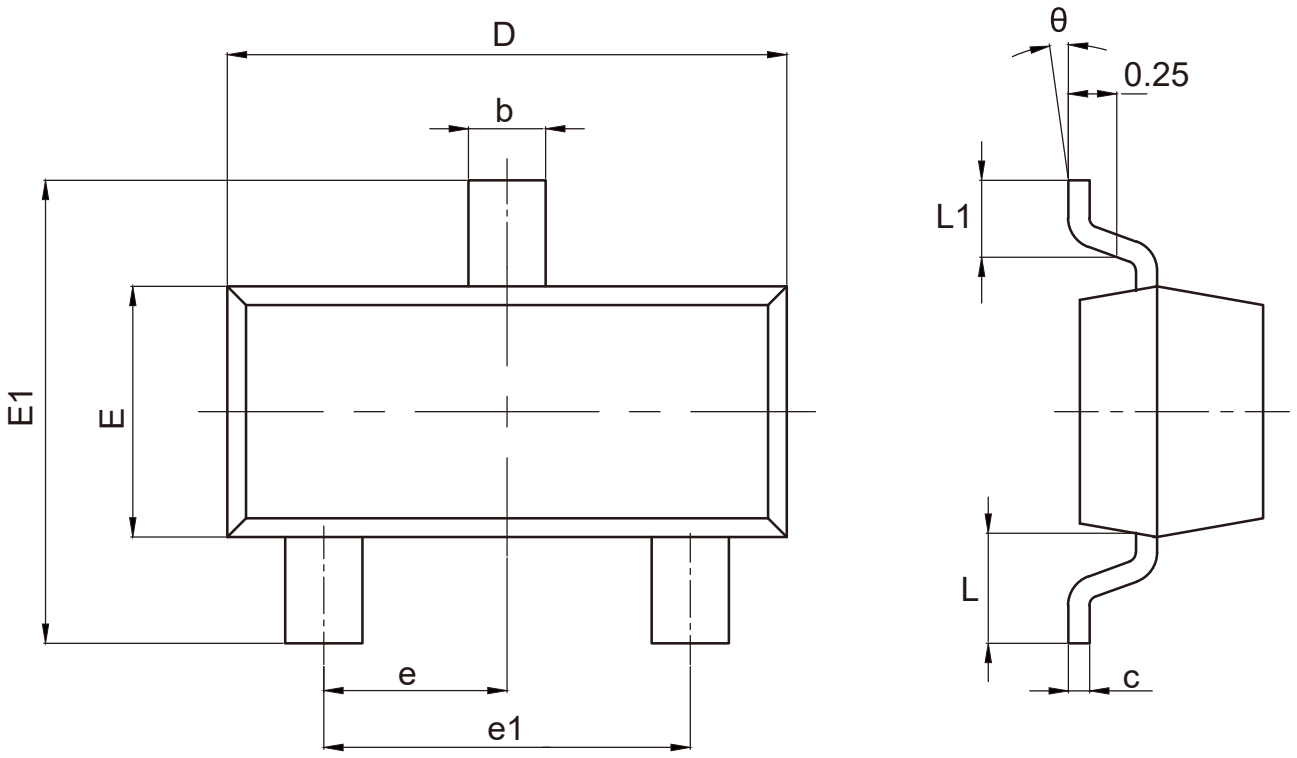
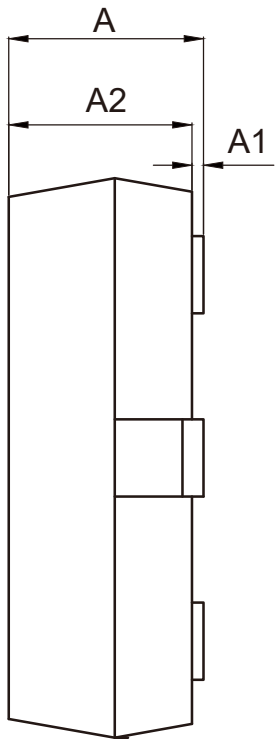


Figure 4: Diode Recovery Test Circuit & Waveform

SOT-23 Package Outline Data



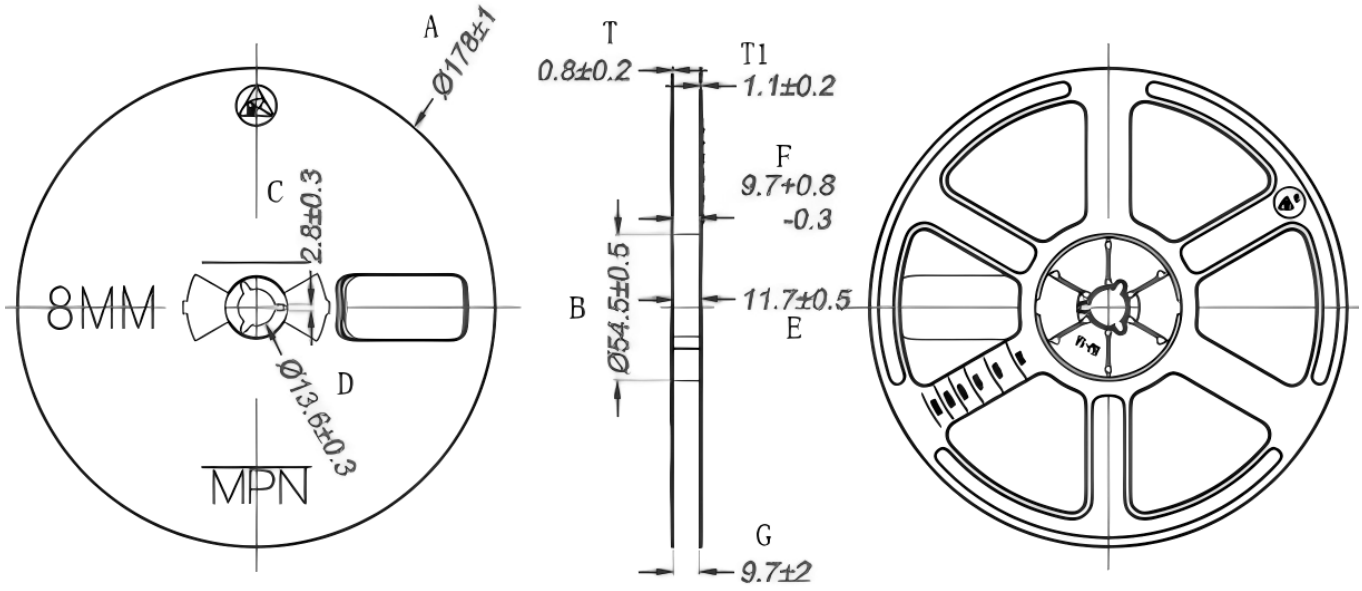


COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER			
SYMBOL	MIN	NOM	MAX
A	0.900	--	1.150
A1	0.000	--	0.100
A2	0.900	--	1.050
c	0.100	--	0.200
b	0.300	0.400	0.500
D	2.800	2.900	3.000
E	1.200	--	1.400
E1	2.250	--	2.550
e	0.950TYP		
e1	1.800	1.900	2.000
L	0.550REF		
L1	0.300	0.400	0.500
θ	0°	--	8°

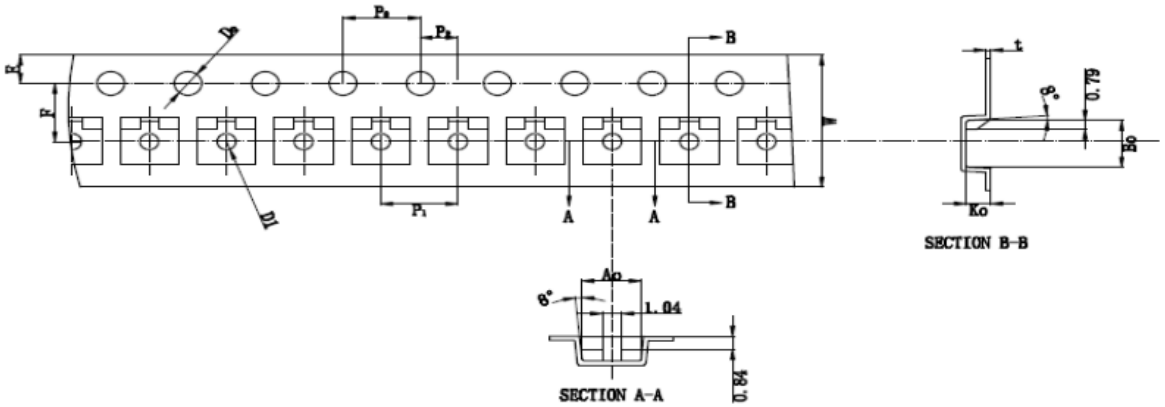
Unit:mm

Tape & Reel Information

Dimensions in mm

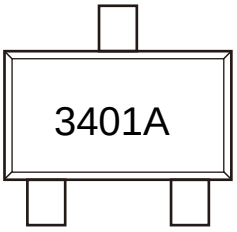


PKG TYPE	W	P	E	F	D	D1	Po	Po10	P2	A0	B0	K0	T
SOT-23	8.00	4.00	1.75	3.50	1.55	1.00	4.00	40.00	2.00	3.17	2.77	1.28	0.20
Tolerance	+0.3/-0.1	±0.1	±0.1	±0.05	±0.1	±0.1	±0.1	±0.2	±0.05	±0.1	±0.1	±0.1	±0.03



Pulling direction

Marking Information：



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2025-07-16	Release of final version

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